BTA208X-800F



3Q Hi-Com Triac
Rev. 07 — 25 January 2011

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This "series F" triac balances the requirements of commutation performance and gate sensitivity. The "less sensitive gate" "series F" is intended for interfacing with low power drivers, including microcontrollers in higher "noise" environments.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Good immunity to false turn-on by dV/dt
- High commutation capability with less sensitive gate
- High voltage capability

- Isolated mounting base package
- Less sensitive gate suitable for higher "noise" environment applications
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

Electronic thermostats

General purpose motor controls

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	65	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73 ^{\circ}\text{C}$; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{ Company of the properties of the$	-	-	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	-	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ Composition}}$	-	-	25	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N .
2	T2	main terminal 2	mb	T2 — T1
3	G	gate		`G sym051
mb	n.c.	mounting base; isolated		
			SOT186A (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BTA208X-800F	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		9 , (
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73$ °C; see Figure 3; see Figure 1; see Figure 2	-	8	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ms$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	65	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	71	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	21	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 0.2 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

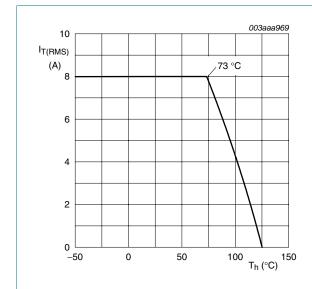


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values

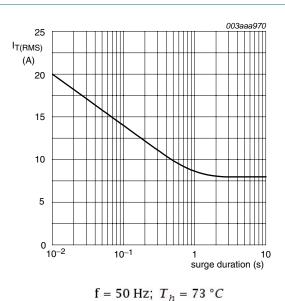


Fig 2. RMS on-state current as a function of surge duration; maximum values

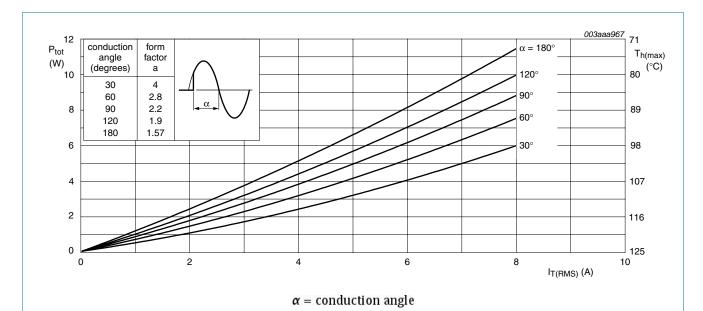


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

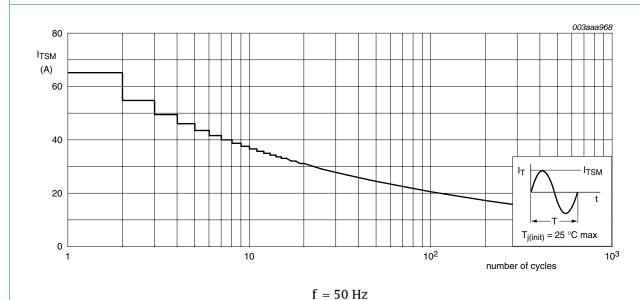
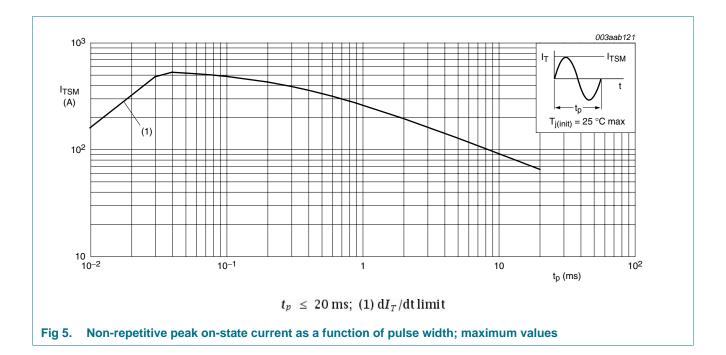


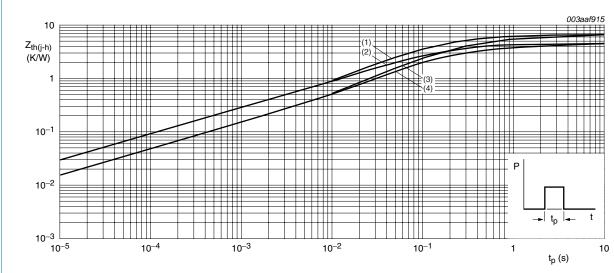
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

Table 6. Isolation characteristics

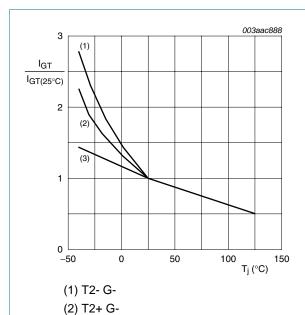
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; $50 \text{ Hz} \le f \le 60 \text{ Hz}$; $RH \le 65 \%$; $T_h = 25 \text{ °C}$	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; $f = 1 \text{ MHz}$; $T_h = 25 ^{\circ}\text{C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	-	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 7}{\text{ Composition}}$	-	-	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 7}{\text{C}}$	-	-	25	mA
I _L latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 8}}{\text{C}}$	-	-	30	mA	
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 8}}{\text{C}}$	-	-	45	mA
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	30	mΑ	
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	-	30	mΑ
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mΑ
Dynamic ch	aracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; exponential waveform; gate open circuit	70	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 0.1 V/µs; gate open circuit; see <u>Figure 12</u>	20	-	-	A/m
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 8 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; \text{ gate open circuit};$ see Figure 12	14	-	-	A/m:

(3) T2+ G+



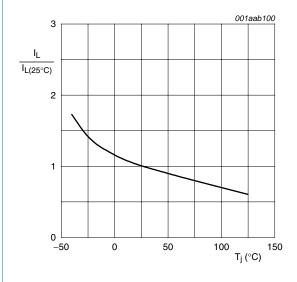
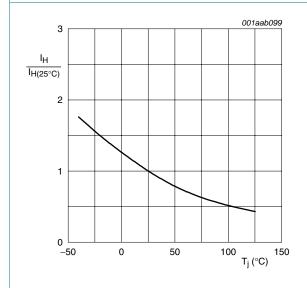
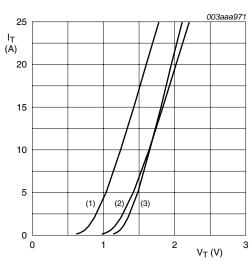


Fig 7. Normalized gate trigger current as a function of junction temperature

Fig 8. Normalized latching current as a function of junction temperature





Normalized holding current as a function of junction temperature

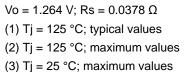


Fig 10. On-state current as a function of on-state voltage

Fig 9.

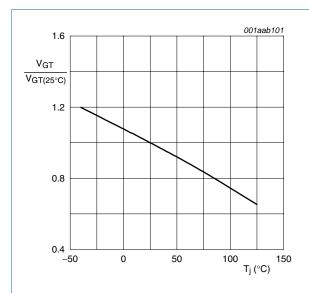


Fig 11. Normalized gate trigger voltage as a function of junction temperature

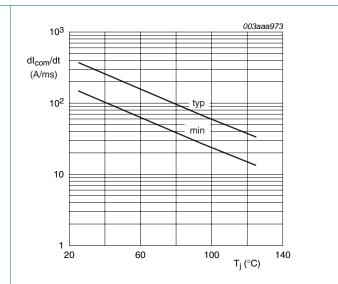
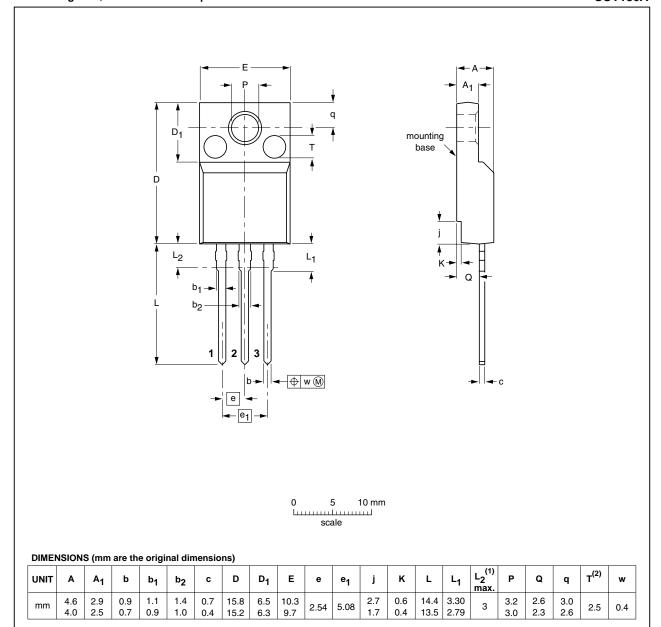


Fig 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT186A		3-lead TO-220F				-02-04-09 06-02-14

Fig 13. Package outline SOT186A (TO-220F)

BTA208X-800F

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA208X-800F v.7	20110125	Product data sheet	-	BTA208X-800F v.6
Modifications:	 Various change 	s to content.		
BTA208X-800F v.6	20101109	Product data sheet	-	BTA208X_SERIES_D_E_F_5

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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